

Burst A/D MUX Delivers Performance and Value for Mobile Designs



Burst A/D MUX CellularRAM® Memory

x16 Burst A/D MUX CellularRAM® Lowers Costs and Saves Design Time

Our x16 burst A/D MUX bare die, pseudo-static RAM device achieves mobile-application performance with a reduced pin count, lowering costs and saving design time. These devices combine the high throughput of DRAM technology with an SRAM-like interface at a much lower cost per bit, making burst A/D MUX CellularRAM an excellent choice for emerging markets.

We offer our burst A/D MUX CellularRAM products in a wide range of densities. Available only as bare die, they're good companion devices for NOR and NAND Flash and are ideally suited for multichip packages (MCPs) and package-on-packages (PoPs). Find out more at www.micron.com.

Why Design with Burst A/D MUX CellularRAM?

1. Variable Latency

Cuts access time in half, making data available as quickly as 35ns.

2. Fixed Latency

Enables compatibility with older systems.

3. Adjustable Output Drive

Enables users to tune outputs to match system impedance and minimize noise and power.

4. Partial-Array Refresh (PAR)

Reduces standby current by refreshing only that part of the memory array required by the host system.

5. On-Board Temperature Sensor

Reduces standby current by automatically adjusting the refresh rate according to the operating temperature of the device.

micron.com

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